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PCN # 170 Notification Date: 8 April 2019

Product / Process Change Notice

Parts Affected:

Chip process, CP773, P-Channel Mosfets, wafers and bare die

Extent of Change:

The CP773 wafer process has been discontinued and replaced with the CP798X wafer process. See figures 1 and 2 for details.

Reason for Change:

The CP773 wafer has been replaced to the CP798X wafer process in order to enhance the manufacturing process controls and performance. In addition, this change is being done to ensure undisrupted supply of product, moving forward.

Effect of Change:

The wafer process meets all electrical specifications of the individual devices listed on the following page.

Qualification:

P/N: CP798X Chip Process Package: SOIC-8

N	lo.	Test	Conditions (Reference standards are in bold)	Qty	Pass/Fail	Test Results	
1		Device Life Tests					
	а	High Temperature Gate Bias (HTGB)	T=150°C, t = 1000 hours 100% V_GS JESD22-A108	80	Pass	80/80	
	b	High Temperature Reverse Bias (HTRB)	T=150°C, t = 1000 hours 80% V_DS JESD22-A108	80	Pass	80/80	

Effective Date of Change:

Existing inventory of Chip Process CP773 will be shipped until depleted.

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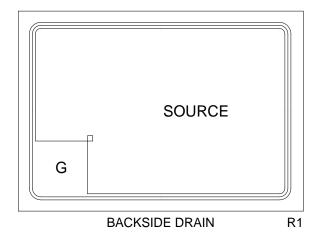
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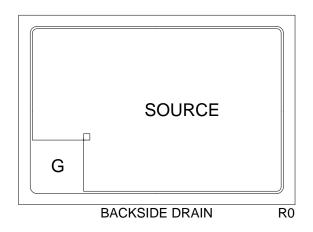
Sample Availability:

Please contact your salesperson or manufacturer's representative for samples.

Figure 1: CP773 Chip Geometry (Discontinued)

Figure 2: CP798X Chip Geometry





Wafer Diameter: 8 inch
Die Size: 39 x 27 mils
Die Thickness: 7.5 mils
Bond Pad Size (Gate): 6.5 x 6.5 mils
Bond Pad Size (Source): 33 x 21 mils
Topside Metal: Al (40,000Å)

Backside Metal: Ti/Ni/Ag (1000Å/3000Å/10000Å)

Wafer Diameter: 8 inch
Die Size: 37.8 x 26 mils
Die Thickness: 5.5 mils
Bond Pad Size (Gate): 7.3 x 7.3 mils
Bond Pad Size (Source): 34 x 22.2 mils
Topside Metal: Al-Cu (40,000Å)

Backside Metal: Ti/Ni/Ag (1000Å/3000Å/10000Å)

Part Numbers Affected:

CEN1232	CP773-CMPDM302PH-WN

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As per JEDEC standard JESD46, Customer Notification of Product/Process Changes by Solid-State Suppliers, a lack of acknowledgement of a PCN within thirty (30) days constitutes acceptance of the change.

The undersigned acknowledges and accepts Central Semiconductor's Product/Process Change Notification (PCN).

Company Name:	
Address:	
Printed Name:	
Title:	
Signature:	
Date:	

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